

WHAT IS CLAIMED IS:

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5 1. A reflective type liquid crystal display device on which display is created by reflecting light incident from the display observation side, comprising:

a display electrode made of a reflective material for reflecting the incident light on a surface thereof; and

a back-surface electrode disposed in contact with a back surface of the display electrode.

10 2. The device according to claim 1, wherein said back-surface electrode is made of a high melting point metal.

15 3. The device according to claim 2, wherein said display electrode is made of aluminum.

20 4. The device according to claim 1, wherein said display electrode and the back-surface electrode are patterned into the same shape.

25 5. The device according to claim 1, further comprising a transistor for controlling current to the display electrode, said back-surface electrode and the transistor being electrically interconnected.

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6. The device according to claim 5, wherein

said transistor is a thin-film transistor which uses a polycrystalline silicon layer formed on a substrate as an active layer, and

a part of the back-surface electrode is connected to said
5 active layer via a contact hole.

7. The device according to claim 6, wherein
said back-surface electrode is made of a high melting
point metal.

8. A method of manufacturing a reflective type liquid
crystal display device on which display is created by
reflecting light incident from the display observation side,
comprising:

a step of forming a back-surface electrode layer;
a step of forming a display electrode layer constituted
of a reflective material on the back-surface electrode layer;
and

a step of patterning the formed back-surface electrode
20 layer and the display electrode layer to form a surface
electrode and a back-surface electrode in the same shape,

to form a display electrode for reflecting the incident
light by a surface thereof and the back-surface electrode
disposed in contact with a back surface of the display
25 electrode.

9. The method according to claim 8, further comprising:

a process of forming a thin film transistor as an active layer of polycrystalline silicon on a substrate;

a step of forming an insulating film to cover the thin film transistor; and

5 a step of forming a contact hole in the insulating film, wherein

said back-surface electrode is formed on a smoothened film with said contact hole formed therein.

10. The method according to claim 9, wherein
said back-surface electrode is made of a high melting point metal.

11. The method according to claim 10, wherein
said high melting point metal is selected from the group consisting of molybdenum, titanium, tungsten, tantalum and chromium, or an alloy thereof.

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